

PSMN012-100YS

N-channel 100V 12mΩ standard level MOSFET in LPAK

Rev. 04 — 23 February 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C; see Figure 1	-	-	60	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	-	130	W
T _j	junction temperature		-55	-	175	°C
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 60 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; unclamped	-	-	170	mJ
Dynamic characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 45 A;	-	19	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 50 V; see Figure 14 and 15	-	64	-	nC

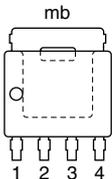
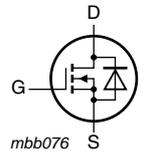


Table 1. Quick reference ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 100\text{ °C};$ see Figure 12	-	-	23	mΩ
		$V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ °C};$ see Figure 13	-	10	12	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

SOT669 (LPAK)

3. Ordering information

Table 3. Ordering information

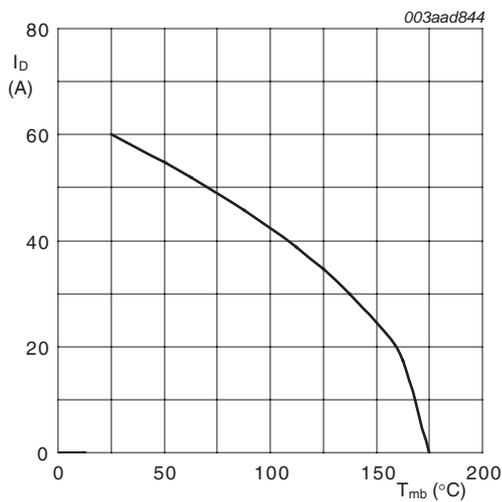
Type number	Package		Version
	Name	Description	
PSMN012-100YS	LPAK	plastic single-ended surface-mounted package (LPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

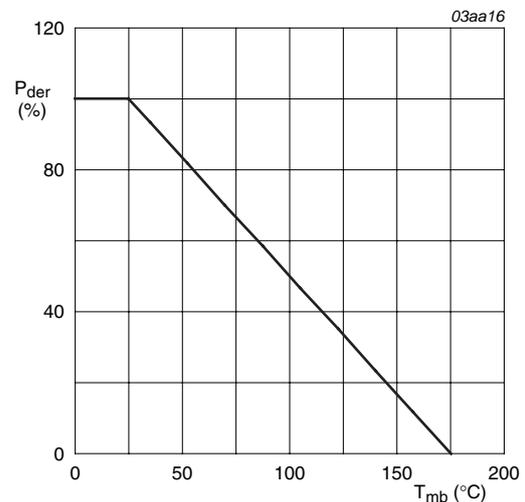
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 100 °C; see Figure 1	-	43	A
		T _{mb} = 25 °C; see Figure 1	-	60	A
I _{DM}	peak drain current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C; see Figure 3	-	242	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	130	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{slid(M)}	peak soldering temperature		-	260	°C
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	60	A
I _{SM}	peak source current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C	-	242	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 60 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; unclamped	-	170	mJ



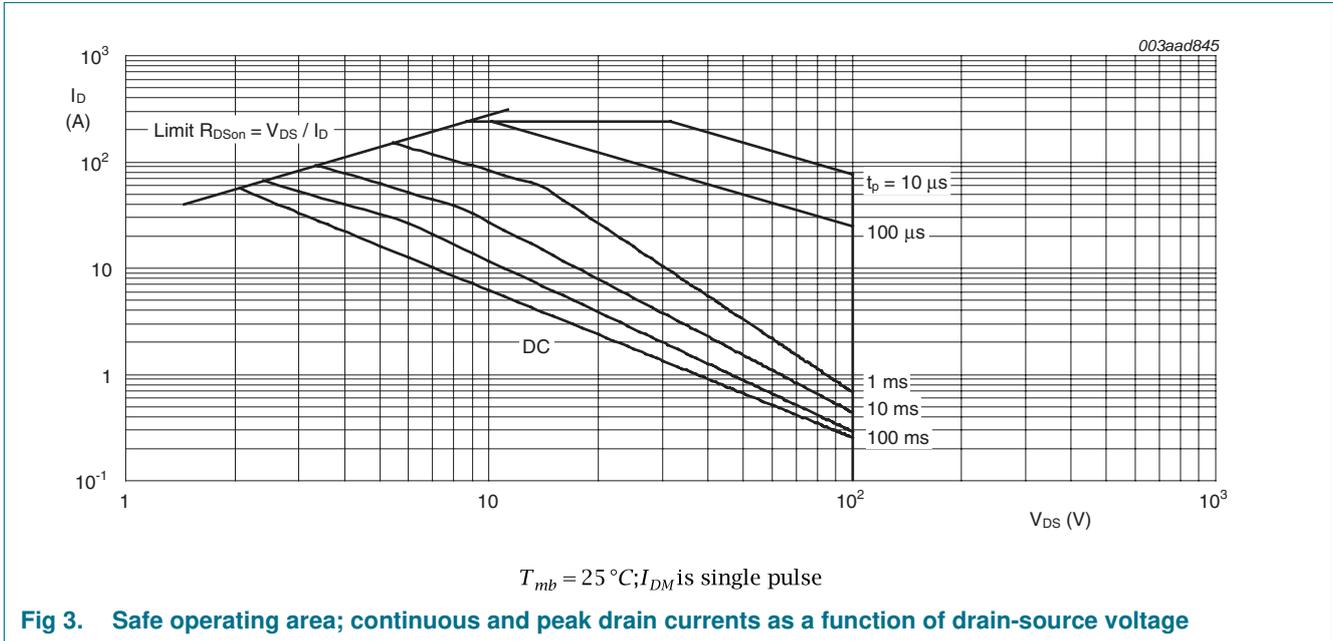
V_{GS} ≥ 10 V

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.5	1.1	K/W

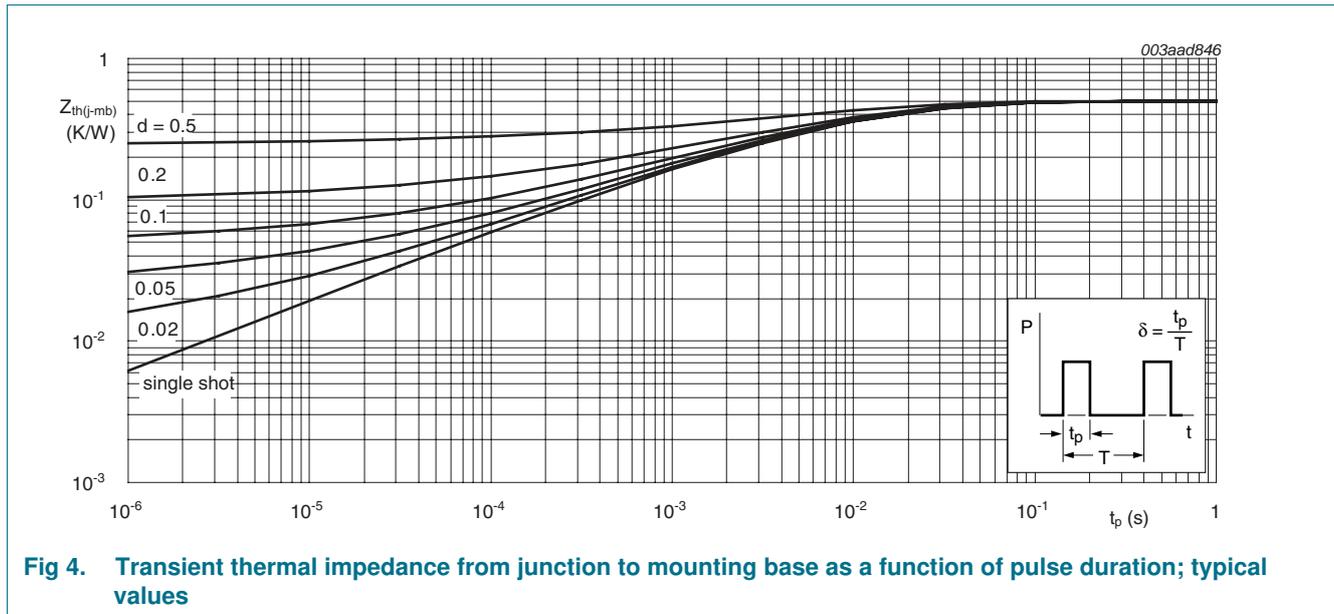


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

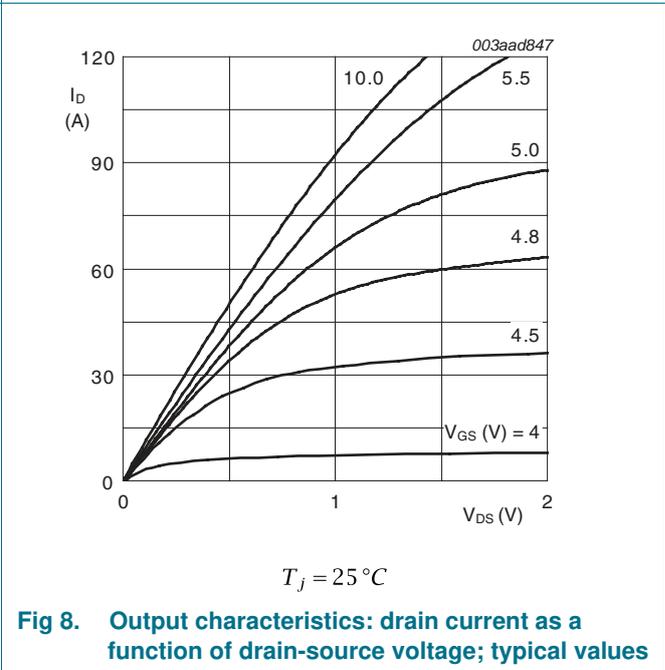
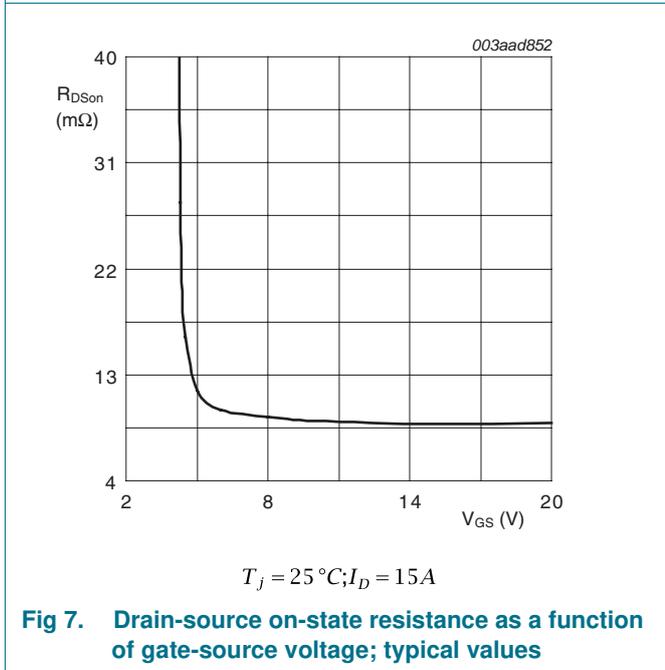
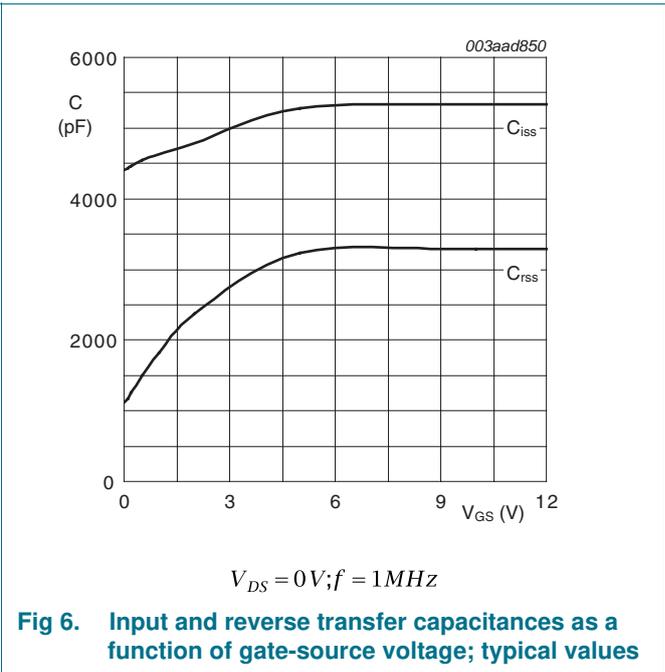
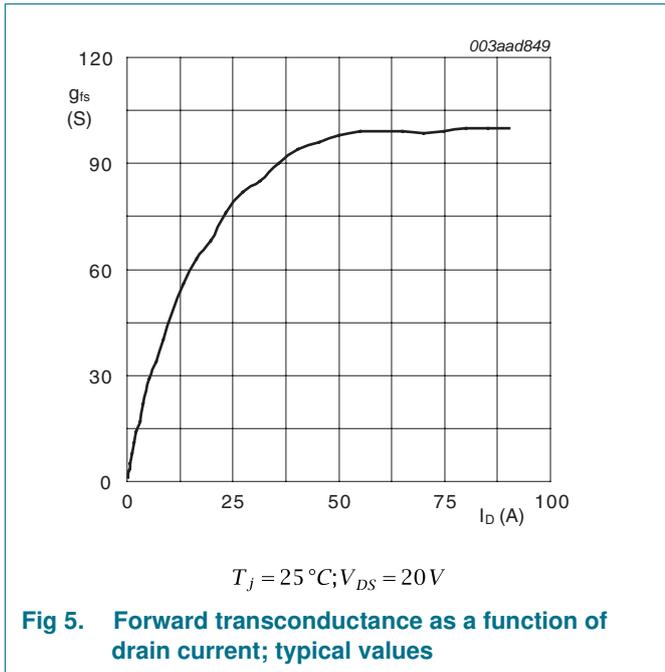
6. Characteristics

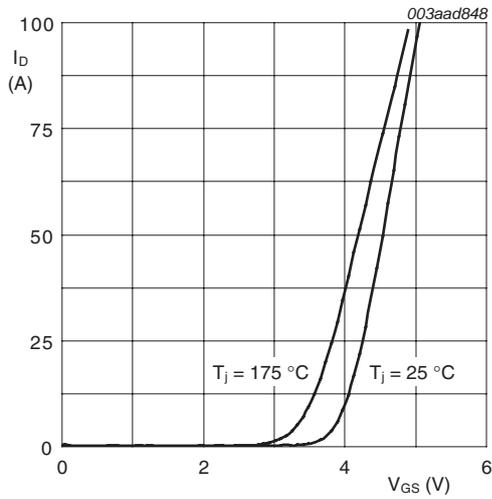
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10	0.95	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 11 and 10	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 10	-	-	4.6	V
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	-	100	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.06	5	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see Figure 12	-	-	23	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 12	-	27	35.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 13	-	10	12	mΩ
R_G	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	0.7	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	51	-	nC
		$I_D = 45 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 and 15	-	64	-	nC
Q_{GS}	gate-source charge		-	14.9	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	$I_D = 45 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	10.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	4.7	-	nC
Q_{GD}	gate-drain charge	$I_D = 45 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 and 15	-	19	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 50 \text{ V};$ see Figure 14 and 15	-	4.4	-	V
C_{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 16	-	3500	-	pF
C_{oss}	output capacitance		-	246	-	pF
C_{rss}	reverse transfer capacitance		-	149	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.1 \text{ }^\circ\Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 4.7 \text{ }^\circ\Omega; T_j = 25 \text{ }^\circ\text{C}$	-	23	-	ns
t_r	rise time		-	31	-	ns
$t_{d(off)}$	turn-off delay time		-	52.5	-	ns
t_f	fall time		-	25	-	ns

Table 6. Characteristics ...continued

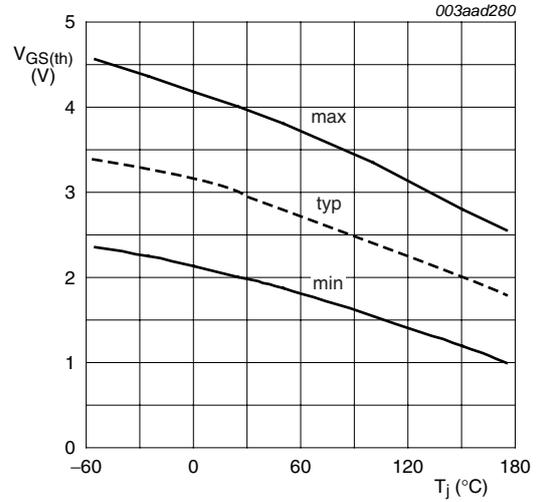
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 15\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; see Figure 17	-	0.8	1.2	V
t_{rr}	reverse recovery time	$I_S = 15\text{ A}$; $di_S/dt = 100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$;	-	56	-	ns
Q_r	recovered charge	$V_{DS} = 50\text{ V}$	-	129	-	nC





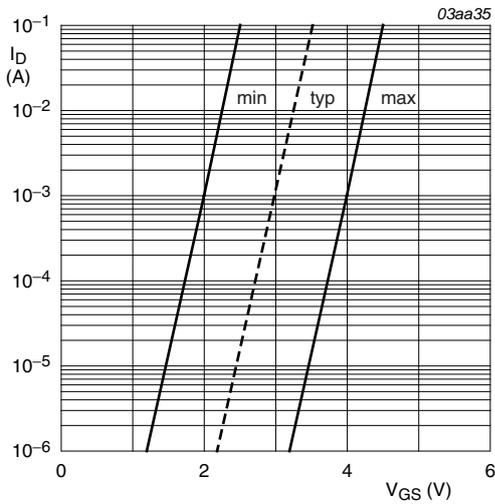
$$V_{DS} > I_D \times R_{DSon}$$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



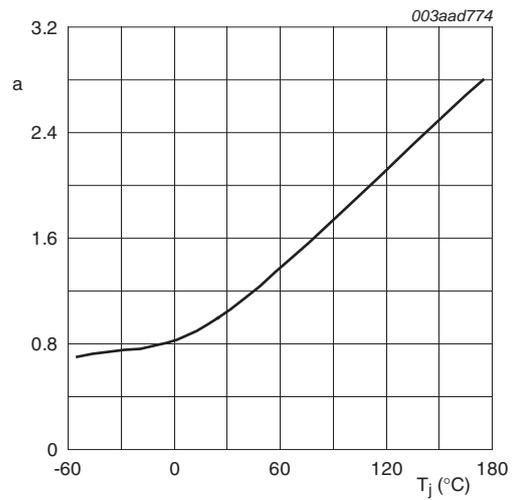
$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



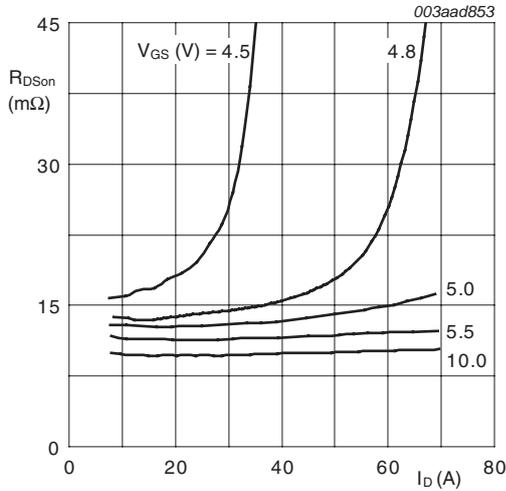
$$T_j = 25 \text{ °C}; V_{DS} = 5 \text{ V}$$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



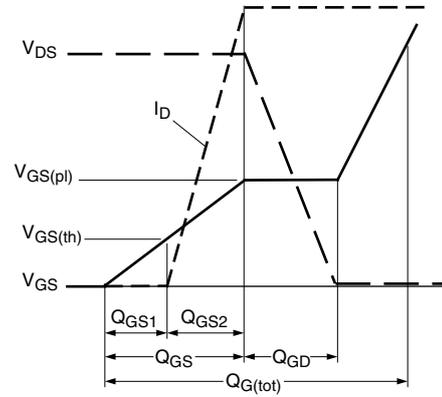
$$a = \frac{R_{DSon}}{R_{DSon(25 \text{ °C})}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



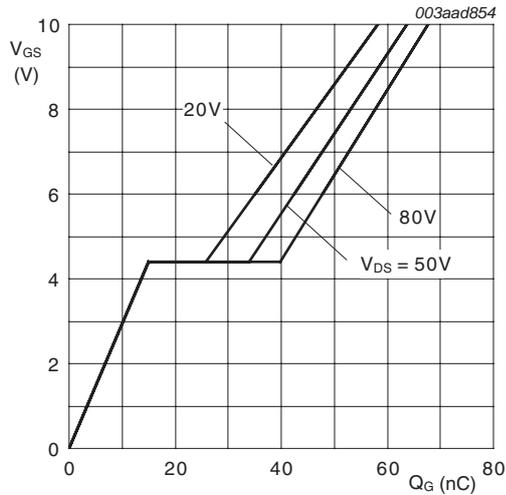
$T_j = 25^\circ C$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values



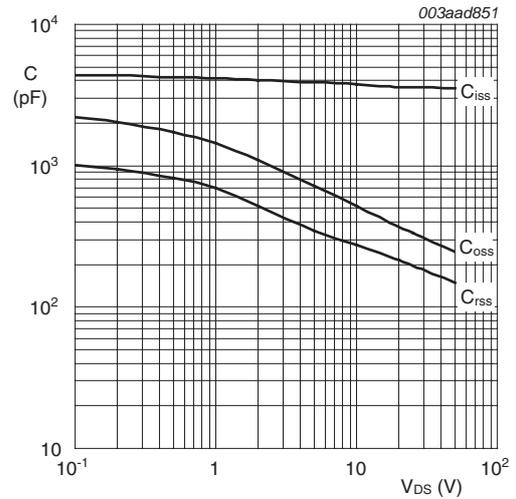
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Fig 14. Gate charge waveform definitions



$T_j = 25^\circ C; I_D = 45A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

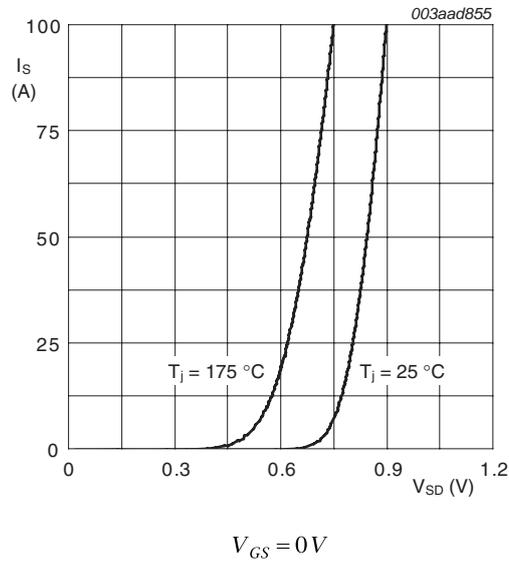


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LPAK); 4 leads

SOT669

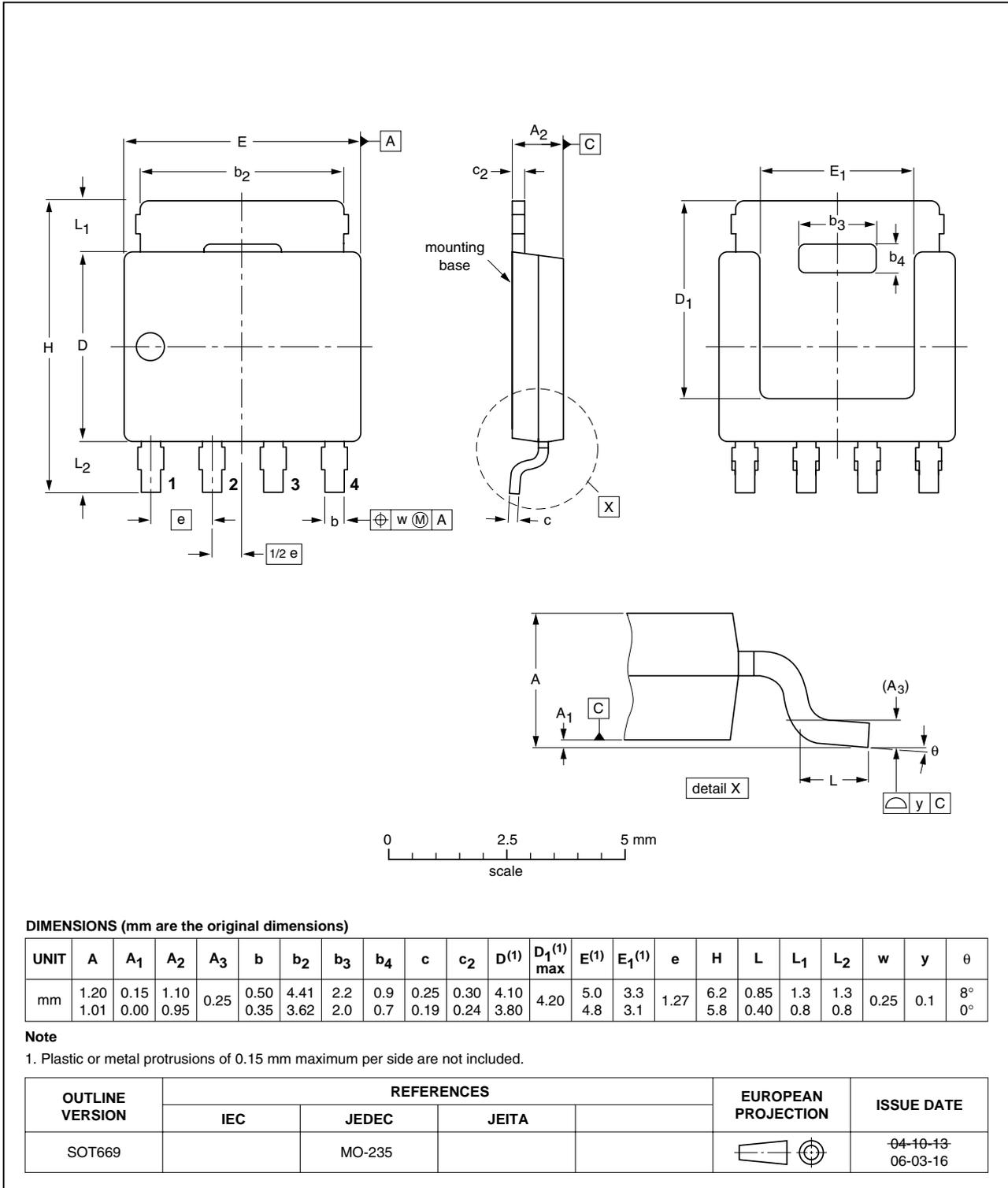


Fig 18. Package outline SOT669 (LPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN012-100YS_4	20100223	Product data sheet	-	PSMN012-100YS_3
Modifications:	• Status changed from objective to product.			
PSMN012-100YS_3	20100107	Product data sheet	-	PSMN012-100YS_2
PSMN012-100YS_2	20091214	Objective data sheet	-	PSMN012-100YS_1
PSMN012-100YS_1	20091022	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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11. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	3
5	Thermal characteristics	5
6	Characteristics	6
7	Package outline	11
8	Revision history	12
9	Legal information	13
9.1	Data sheet status	13
9.2	Definitions	13
9.3	Disclaimers	13
9.4	Trademarks	14
10	Contact information	14

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